

# Zihao Deng

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Alloy-Free Band Gap Tuning across the Visible Spectrum. <i>Physical Review Letters</i> , 2019, 122, 256403.	7.8	37
2	Deep Ultraviolet Luminescence Due to Extreme Confinement in Monolayer GaN/Al(GaN) Nanowire and Planar Heterostructures. <i>Nano Letters</i> , 2019, 19, 7852-7858.	9.1	35
3	Semiconducting High-Entropy Chalcogenide Alloys with Ambi-ionic Entropy Stabilization and Ambipolar Doping. <i>Chemistry of Materials</i> , 2020, 32, 6070-6077.	6.7	35
4	Boron arsenide heterostructures: lattice-matched heterointerfaces and strain effects on band alignments and mobility. <i>Npj Computational Materials</i> , 2020, 6, .	8.7	28
5	Toward the predictive discovery of ambipolarly dopable ultra-wide-band-gap semiconductors: The case of rutile GeO <sub>2</sub> . <i>Applied Physics Letters</i> , 2021, 118, .	3.3	23
6	Oxygen defect dominated photoluminescence emission of ScAl <sub>1-x</sub> N grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	22
7	Controlling Defect Formation of Nanoscale AlN: Toward Efficient Current Conduction of Ultrawide-Bandgap Semiconductors. <i>Advanced Electronic Materials</i> , 2020, 6, 2000337.	5.1	19
8	High electron mobility of Al <sub>x</sub> Ga <sub>1-x</sub> N evaluated by unfolding the DFT band structure. <i>Applied Physics Letters</i> , 2020, 117, 242105.	3.3	17
9	Experimental and theoretical study of hole scattering in RF sputtered p-type Cu <sub>2</sub> O thin films. <i>Applied Physics Letters</i> , 2022, 120, .	3.3	5
10	Cation-size mismatch as a predictive descriptor for structural distortion, configurational disorder, and valence-band splitting in II-IV-N <sub>2</sub> semiconductors. <i>Applied Physics Letters</i> , 2021, 119, .	3.3	4
11	Semiconducting character of LaN: Magnitude of the bandgap and origin of the electrical conductivity. <i>AIP Advances</i> , 2021, 11, .	1.3	2